

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-10. (canceled)

11. (previously presented) A multilayer stack comprising:

a dielectric layer and one or more surrounding dielectric layers situated above or below the dielectric layer, a dielectric constant of the dielectric layer being greater than a dielectric constant of the surrounding dielectric layers, and

a metallization structure which is arranged on the dielectric layer and is arranged at a distance from a ground electrode, wherein the metallization structure has a capacitor electrode and a line that acts as a coil, where the capacitor electrode and the line are arranged in a common plane which lies parallel to the ground electrode at a distance h_1 , and wherein:

$$\frac{w}{h_1} > 3,$$

where w is the width of the line, wherein:

$$\frac{\epsilon_{medium} \cdot d_{\epsilon}}{\epsilon \cdot d_{medium}} > 5$$

wherein the dielectric constant of and a thickness of the dielectric layer are ϵ_{medium} and d_{medium} , respectively, and the dielectric constant of and a thickness of the surrounding dielectric layers are ϵ and d_{ϵ} , respectively.

12. (previously presented) A metallization structure as claimed in claim 11, further comprising:

a second ground electrode, the common plane comprising the capacitor electrode and the line being arranged parallel to said second ground electrode at a distance h_2 , and the common plane comprising the capacitor electrode and the line being between the first and second ground electrodes, where

$$\frac{w}{h_2} > 3.$$

13. (previously presented) A multilayer stack as claimed in claim 12, further comprising one or more additional metallization structures in the common plane, wherein

$$\frac{\epsilon_{\text{medium}} \cdot d_{\text{min}}}{\epsilon \cdot d_{\text{medium}}} > 7,$$

where d_{min} is the minimum distance to a nearest metallization structure in the plane, and wherein the dielectric constant of and a thickness of the dielectric layer are ϵ_{medium} and d_{medium} , respectively, and the dielectric constant of the surrounding dielectric layers is ϵ .

14. (currently amended) A multilayer stack as claimed in claim 12, wherein the multilayer stack further comprises magnetic layers.

15. (previously presented) A multilayer stack as claimed in claim 12, produced in a multilayer laminate process.

16. (previously presented) A multilayer stack as claimed in claim 12, produced in a Low Temperature Cofire Ceramic (LTCC) process.

17. (previously presented) A multilayer stack comprising:

a dielectric layer and one or more surrounding dielectric layers situated above or below the dielectric layer, a dielectric constant of the dielectric layer being greater than a dielectric constant of the surrounding dielectric layers, and

a metallization structure which is arranged on the dielectric layer and is arranged at a distance from a ground electrode, wherein the metallization structure has a capacitor electrode and a line that acts as a coil, where the capacitor electrode and the line are arranged in a common plane which lies parallel to the ground electrode at a distance h_1 , and wherein:

$$\frac{w}{h_1} > 3,$$

where w is the width of the line, wherein the multilayer stack is produced in a Low Temperature Cofire Ceramic (LTCC) process.

18. (previously presented) A metallization structure as claimed in claim 17, further comprising:

a second ground electrode, the common plane comprising the capacitor electrode and the line being arranged parallel to said second ground electrode at a distance h_2 , and the common plane comprising the capacitor electrode and the line being between the first and second ground electrodes, where

$$\frac{w}{h_2} > 3.$$

19. (previously presented) A multilayer stack as claimed in claim 18, further comprising one or more additional metallization structures in the common plane, wherein

$$\frac{\epsilon_{\text{medium}} \cdot d_{\text{min}}}{\epsilon \cdot d_{\text{medium}}} > 7,$$

where d_{min} is the minimum distance to a nearest metallization structure in the plane, and wherein the dielectric constant of and a thickness of the dielectric layer are ϵ_{medium} and d_{medium} , respectively, and the dielectric constant of the surrounding dielectric layers is ϵ .

20. (currently amended) A multilayer stack as claimed in claim 18, wherein the multilayer stack further comprises magnetic layers.

21. (previously presented) A multilayer stack as claimed in claim 18, produced in a multilayer laminate process.

22. (new) A multilayer stack comprising:

a dielectric layer and one or more surrounding dielectric layers situated above or below the dielectric layer, a dielectric constant of the dielectric layer being greater than a dielectric constant of the surrounding dielectric layers;

a metallization structure which is arranged on the dielectric layer and is arranged at a distance from a ground electrode, wherein the metallization structure has a capacitor electrode and a line that acts as a coil, where the capacitor electrode and the line are arranged in a common plane which lies parallel to the ground electrode at a distance h_1 , and wherein

$$\frac{w}{h_1} > 3,$$

where w is the width of the line;

a second ground electrode, the common plane comprising the capacitor electrode and the line being arranged parallel to said second ground electrode at a distance h_2 , and the common plane comprising the capacitor electrode and the line being between the first and second ground electrodes, where

$$\frac{w}{h_2} > 3; \text{ and}$$

one or more additional metallization structures in the common plane, wherein

$$\frac{\epsilon_{\text{medium}} \cdot d_{\text{min}}}{\epsilon \cdot d_{\text{medium}}} > 7,$$

where d_{min} is the minimum distance to a nearest metallization structure in the plane, and wherein the dielectric constant of and a thickness of the dielectric layer are ϵ_{medium} and d_{medium} , respectively, and the dielectric constant of the surrounding dielectric layers is ϵ .

23. (new) The multilayer stack of claim 22,

$$\frac{\epsilon_{\text{medium}} \cdot d_e}{\epsilon \cdot d_{\text{medium}}} > 5$$

wherein the dielectric constant of and a thickness of the dielectric layer are ϵ_{medium} and d_{medium} , respectively, and the dielectric constant of and a thickness of the surrounding dielectric layers are ϵ and d_e , respectively.

24. (new) The multilayer stack of claim 22, wherein the multilayer stack further comprises magnetic layers.

25. (new) The multilayer stack of claim 22, wherein the multilayer stack is produced in a multilayer laminate process.

26. (new) The multilayer stack of claim 22, wherein the multilayer stack is produced in a LTCC process.

27. (new) A multilayer stack comprising:

a dielectric layer and one or more surrounding dielectric layers situated above or below the dielectric layer, a dielectric constant of the dielectric layer being greater than a dielectric constant of the surrounding dielectric layers;

a metallization structure which is arranged on the dielectric layer and is arranged at a distance from a ground electrode, wherein the metallization structure has a capacitor electrode and a line that acts as a coil, where the capacitor electrode and the line are arranged in a common plane which lies parallel to the ground electrode at a distance h_1 , and wherein

$$\frac{w}{h_1} > 3,$$

where w is the width of the line;

a second ground electrode, the common plane comprising the capacitor electrode and the line being arranged parallel to said second ground electrode at a distance h_2 , and

the common plane comprising the capacitor electrode and the line being between the first and second ground electrodes, where

$$\frac{w}{h_2} > 3; \text{ and}$$

magnetic layers.

28. (new) The multilayer stack of claim 27,

$$\frac{\epsilon_{\text{medium}} \cdot d_{\epsilon}}{\epsilon \cdot d_{\text{medium}}} > 5$$

wherein the dielectric constant of and a thickness of the dielectric layer are ϵ_{medium} and d_{medium} , respectively, and the dielectric constant of and a thickness of the surrounding dielectric layers are ϵ and d_{ϵ} , respectively.

29. (new) The multilayer stack of claim 27, wherein the multilayer stack is produced in a multilayer laminate process.

30. (new) The multilayer stack of claim 27, wherein the multilayer stack is produced in a LTCC process.